MOSFETs Silicon P-Channel MOS (U-MOSⅥ)

XPN52016MC

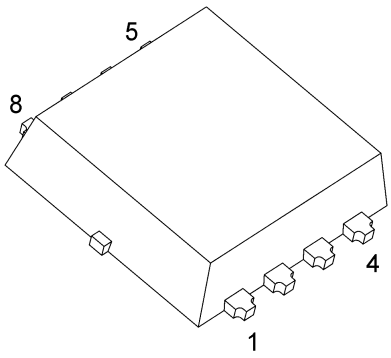
1. Applications

- Automotive
- Switching Voltage Regulators
- DC-DC Converters
- Motor Drivers

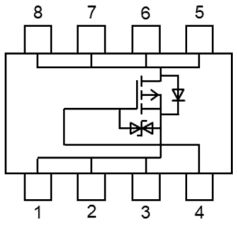
2. Features

(1) AEC-Q101 qualified
(2) Small, thin package
(3) Low drain-source on-resistance: $R_{DS(ON)}$ = 40.0 mΩ (typ.) (V_{GS} = -10 V)
(4) Low leakage current: I_{DSS} = -10 μA (max) (V_{DS} = -60 V)
(5) Enhancement mode: V_{th} = -1.0 to -2.1 V (V_{DS} = -10 V, I_D = -0.2 mA)

3. Packaging and Internal Circuit



TSON Advance(WF)



1, 2, 3: Source
4: Gate
5, 6, 7, 8: Drain

Start of commercial production
2024-10

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4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

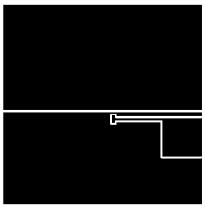
Characteristics			Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	-60	V
Gate-source voltage			V_{GSS}	+10/-20	
Drain current (DC)		(Note 1)	I_D	-15	A
Drain current (pulsed)		(Note 1)	I_{DP}	-30	
Power dissipation	(T_c = 25 °C)		P_D	65	W
Power dissipation	(t = 10 s)	(Note 2)		2.27	
Power dissipation	(t = 10 s)	(Note 3)		0.84	
Single-pulse avalanche energy		(Note 4)	E_{AS}	20	mJ
Single-pulse avalanche current			I_{AS}	-15	A
Channel temperature		(Note 5)	T_{ch}	175	°C
Storage temperature		(Note 5)	T_{stg}	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

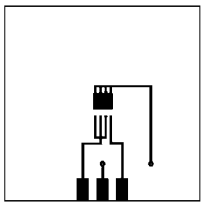
Characteristics			Symbol	Max	Unit
Channel-to-case thermal impedance	(T_c = 25 °C)		$z_{th(ch-c)}$	2.3	°C/W
Channel-to-ambient thermal impedance	(t = 10 s)	(Note 2)	$z_{th(ch-a)}$	66	
Channel-to-ambient thermal impedance	(t = 10 s)	(Note 3)	$z_{th(ch-a)}$	178	

Note 1: Ensure that the channel temperature does not exceed 175 °C.
Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1
Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2
Note 4: V_{DD} = -48 V, T_{ch} = 25 °C (initial), L = 67 μH, R_G = 25 Ω, I_{AS} = -15 A, V_{GS} = 0/-15 V
Note 5: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.



FR-4
25.4 × 25.4 × 0.8
(Unit: mm)

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)



FR-4
25.4 × 25.4 × 0.8
(Unit: mm)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

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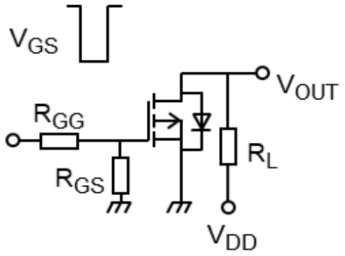
6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	V_{GS} = +10/-16 V, V_{DS} = 0 V	—	—	±10	μA
Drain cut-off current	I_{DSS}	V_{DS} = -60 V, V_{GS} = 0 V	—	—	-10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	I_D = -10 mA, V_{GS} = 0 V	-60	—	—	V
	$V_{(BR)DSX}$	I_D = -10 mA, V_{GS} = 10 V	-50	—	—	
Gate threshold voltage	V_{th}	V_{DS} = -10 V, I_D = -0.2 mA	-1.0	—	-2.1	
Drain-source on-resistance	$R_{DS(ON)}$	V_{GS} = -4.5 V, I_D = -7.5 A	—	44.0	66.0	mΩ
		V_{GS} = -10 V, I_D = -7.5 A	—	40.0	52.0	

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	V_{DS} = -10 V, V_{GS} = 0 V, f = 1 MHz	—	1680	2360	pF
Reverse transfer capacitance	C_{rss}		—	130	182	
Output capacitance	C_{oss}		—	170	—	
Gate resistance	r_g		—	13	26	Ω
Switching time (rise time)	t_r	See Fig. 6.2.1	—	25	—	ns
Switching time (turn-on time)	t_{on}		—	33	—	
Switching time (fall time)	t_f		—	108	—	
Switching time (turn-off time)	t_{off}		—	401	—	



V_{DD} ≈ -30 V
V_{GS} = 0/-10 V
I_D = -7.5 A
R_L = 4.0 Ω
R_{GG} = R_{GS} = 50 Ω
Duty ≤ 1 %, t_w = 10 μs

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	V_{DD} ≈ -48 V, V_{GS} = -10 V, I_D = -15 A	—	47	—	nC
Gate-source charge 1	Q_{gs1}		—	4	—	
Gate-drain charge	Q_{gd}		—	12	—	

6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (DC)	(Note 6)	I_{DR}	—	—	—	-15	A
Reverse drain current (pulsed)	(Note 6)	I_{DRP}	—	—	—	-30	
Diode forward voltage		V_{DSF}	I_{DR} = -15 A, V_{GS} = 0 V	—	—	1.2	V
Reverse recovery time		t_{rr}	I_{DR} = -15 A, V_{GS} = 0 V dI_{DR}/dt = 50 A/μs	—	40	—	ns
Reverse recovery charge		Q_{rr}		—	20	—	nC

Note 6: Ensure that the channel temperature does not exceed 175 °C.

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7. Marking

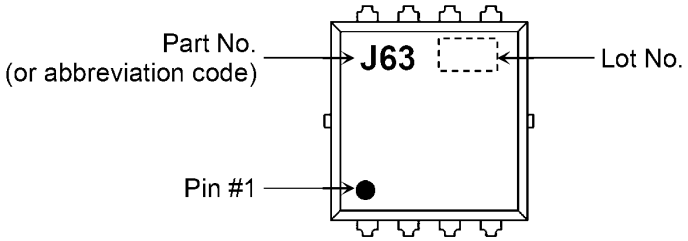


Fig. 7.1 Marking

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8. Characteristics Curves (Note)

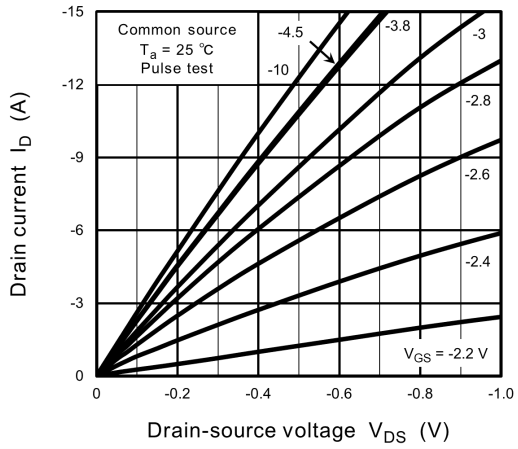


Fig. 8.1 I_D - V_{DS}

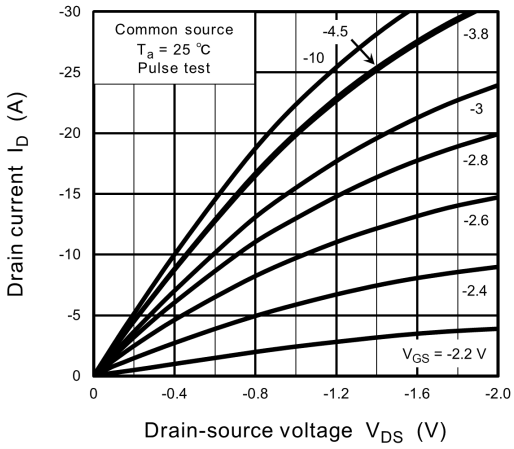


Fig. 8.2 I_D - V_{DS}

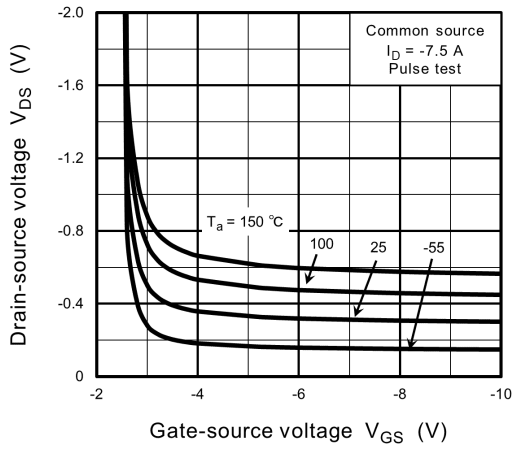


Fig. 8.3 V_{DS} - V_{GS}

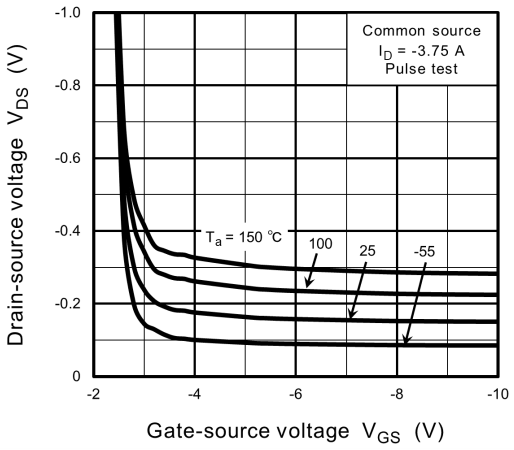


Fig. 8.4 V_{DS} - V_{GS}

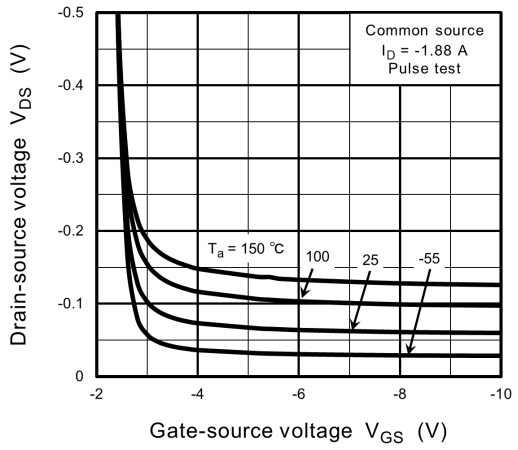


Fig. 8.5 V_{DS} - V_{GS}

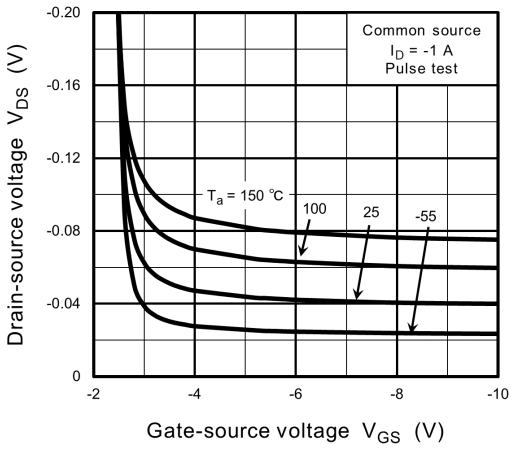


Fig. 8.6 V_{DS} - V_{GS}

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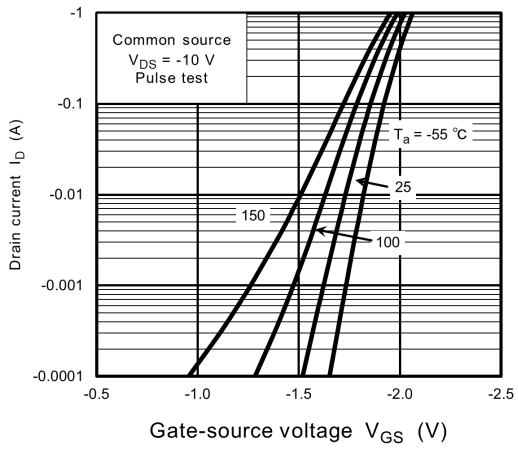


Fig. 8.7 I_D - V_{GS}

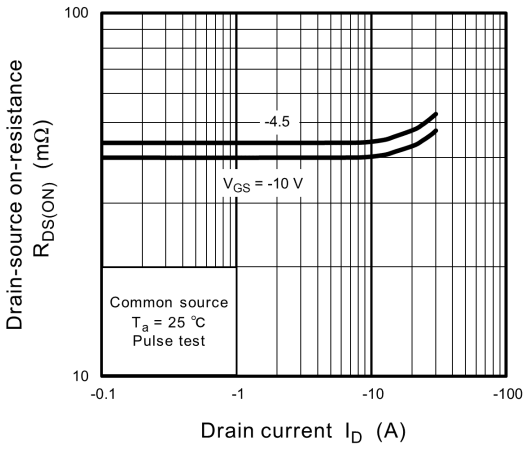


Fig. 8.8 $R_{DS(ON)}$ - I_D

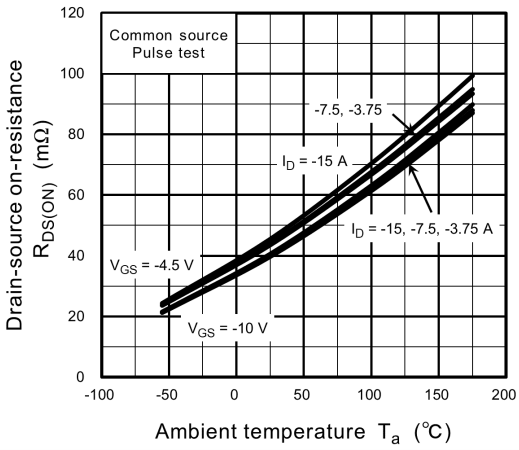


Fig. 8.9 $R_{DS(ON)}$ - T_a

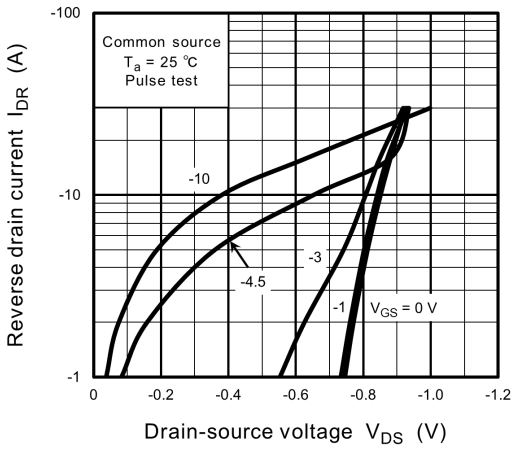


Fig. 8.10 I_{DR} - V_{DS}

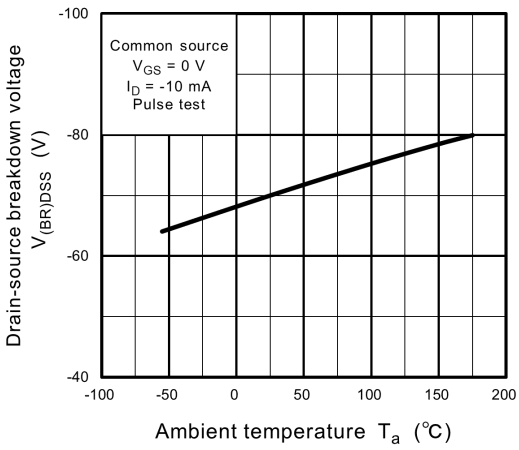


Fig. 8.11 $V_{(BR)DSS}$ - T_a

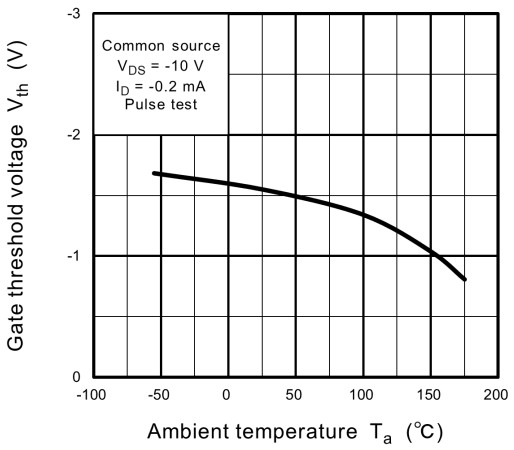


Fig. 8.12 V_{th} - T_a

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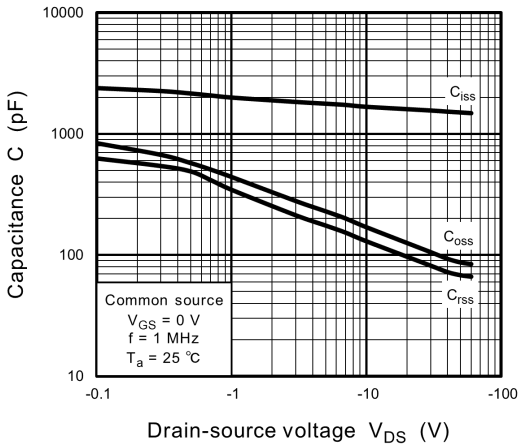


Fig. 8.13 Capacitance - V_{DS}

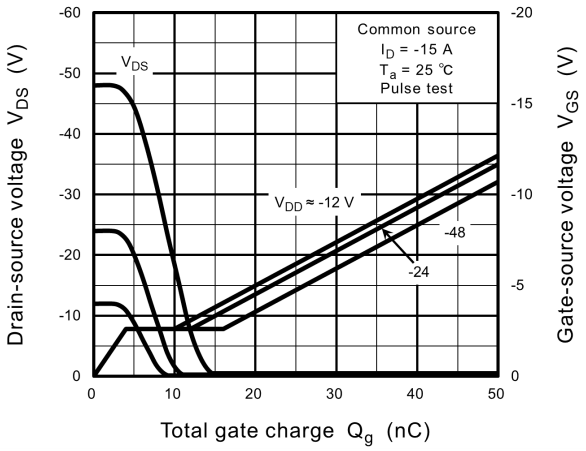


Fig. 8.14 Dynamic Input/Output Characteristics

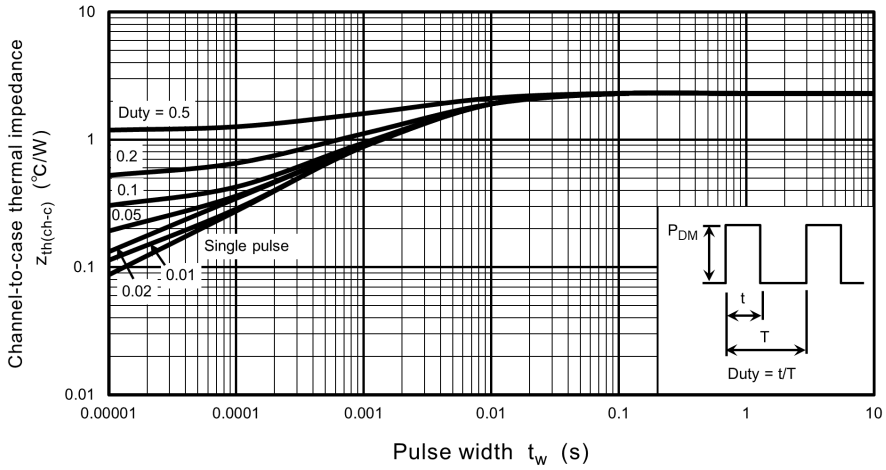


Fig. 8.15 $z_{th(ch-c)}$ - t_w (Guaranteed Maximum)

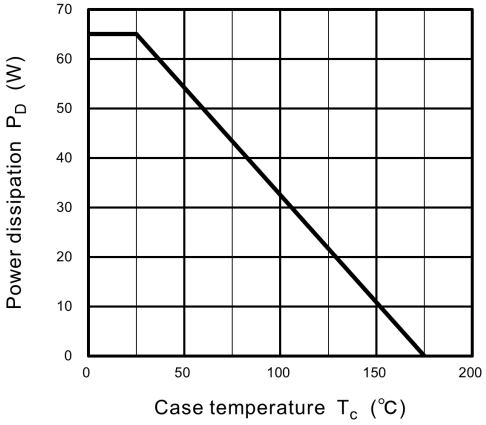


Fig. 8.16 P_D - T_c (Guaranteed Maximum)

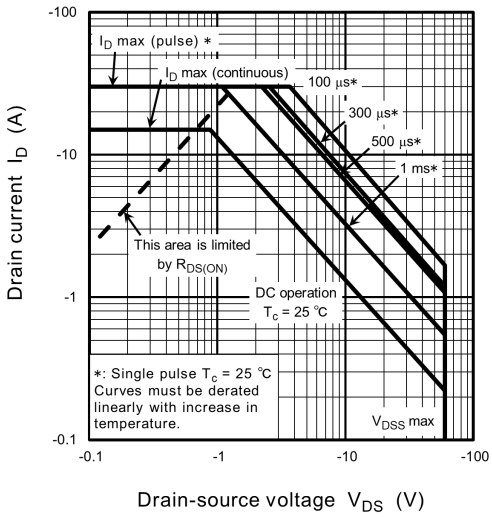


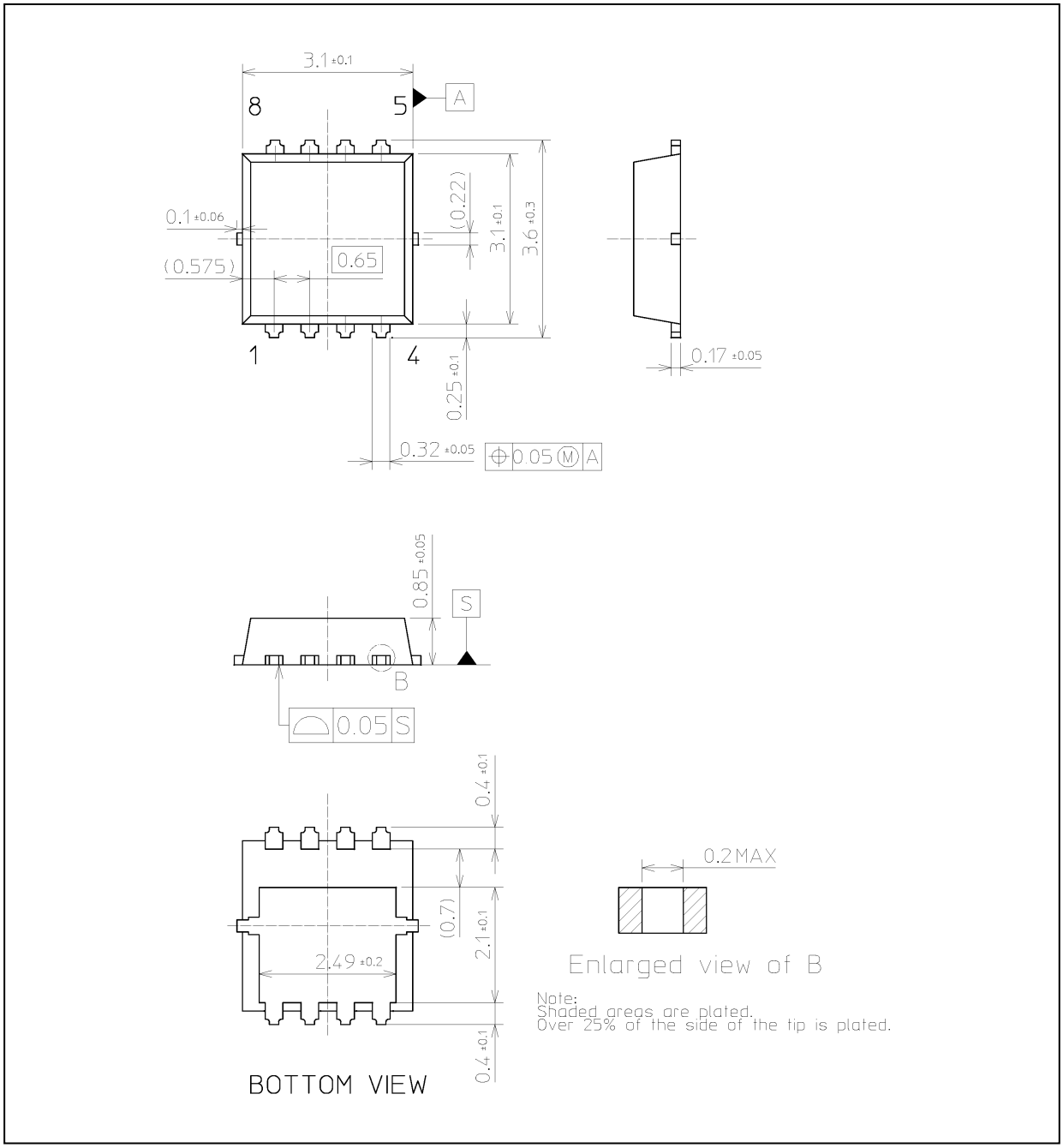
Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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Package Dimensions

Unit: mm



Weight: 0.026 g (typ.)

Package Name(s)
TOSHIBA: 2-3X2A
Nickname: TSON Advance(WF)

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